AR0554S8
4-Line Low Capacitance TVS Diode Array

Description

The AR0554S8 is a low capacitance TVS array, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive high-speed data lines. The AR0554S8 complies with the IEC 61000-4-2 (ESD) with ±30kV air and ±30kV contact discharge. The leads are finished with lead-free matte tin. Each device will protect up to four high-speed lines. The combination of small size, low capacitance, and high surge capability makes them ideal for use in applications such as 10/100 Ethernet, USB 2.0, and visual interfaces.

Features

- Low capacitance: 5pF typical
- Ultra low leakage: nA level
- Low operating voltage: 5V
- Complies with following standards:
  - IEC 61000-4-2 (ESD) immunity test
    - Air discharge: ±30kV
    - Contact discharge: ±30kV
  - IEC61000-4-5 (Lightning) 20A (8/20μs)
- RoHS Compliant

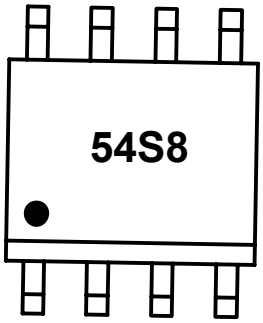
Mechanical Characteristics

- Package: SO-8
- Lead Finish: Matte Tin
- Case Material: “Green” Molding Compound
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections: See Diagram Below
- Marking Information: See Below

Applications

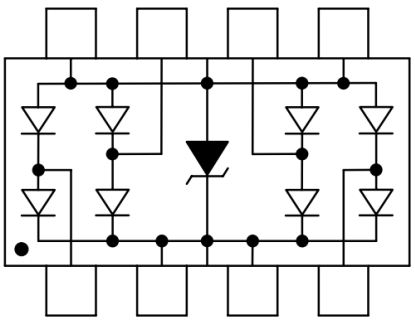
- USB 2.0 power and data line
- Monitors and flat panel displays
- Set-top box and digital TV
- Video graphics cards
- Digital visual interface (DVI)
- Notebook Computers
- SIM Ports
- 10/100 Ethernet
- IEEE 1394 firewire ports

Marking Information



54S8= Device Marking Code
Dot denotes Pin1

Dimensions and Pin Configuration



Circuit and Pin Schematic

Ordering Information

Part Number	Packaging	Reel Size
AR0554S8	2500/Tape & Reel	13 inch

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Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20μs)	Ppk	350	W
Peak Pulse Current (8/20μs)	I_{PP}	20	A
ESD per IEC 61000−4−2 (Air) ESD per IEC 61000−4−2 (Contact)	V_{ESD}	±30 ±30	kV
Operating Temperature Range	T_J	−55 to +150	°C
Storage Temperature Range	Tstg	−55 to +150	°C

Electrical Characteristics (T_A=25°C unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V_{RWM}			5	V	
Breakdown Voltage	V_{BR}	6			V	I_T = 1mA
Reverse Leakage Current	I_R			1	μA	V_{RWM} = 5V
Clamping Voltage	V_C			9	V	I_{PP} = 1A (8 x 20μs pulse), any I/O pin to ground
Clamping Voltage	V_C			17.5	V	I_{PP} = 20A (8 x 20μs pulse), any I/O pin to ground
Junction Capacitance	C_J		3.0	5.0	pF	VR = 0V, f = 1MHz, any I/O pin to ground

Note 1: I/O pins are Pin 1, 3, 4 and 6

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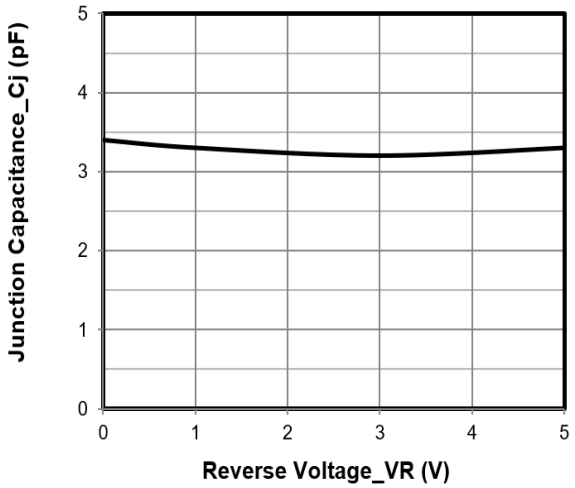
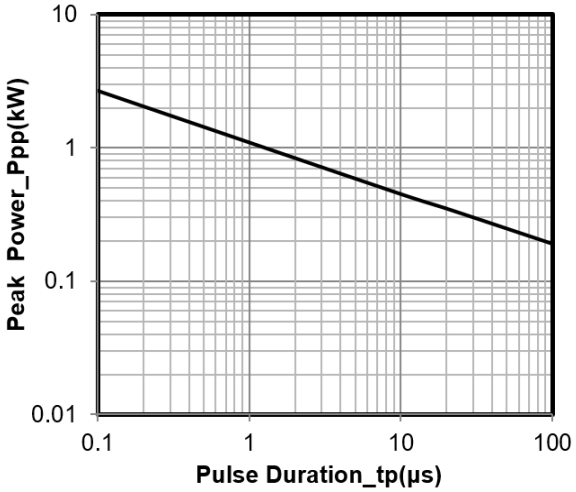
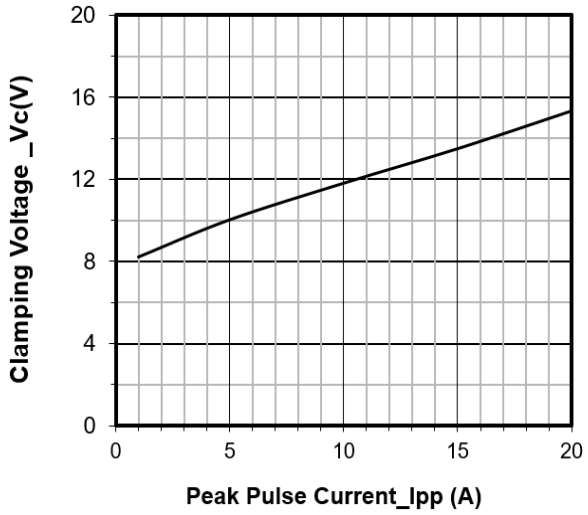
Typical Performance Characteristics (T_A=25°C unless otherwise Specified)



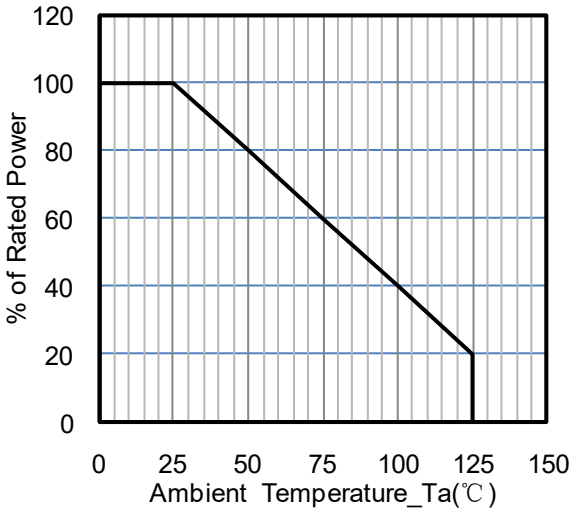
Junction Capacitance vs. Reverse Voltage



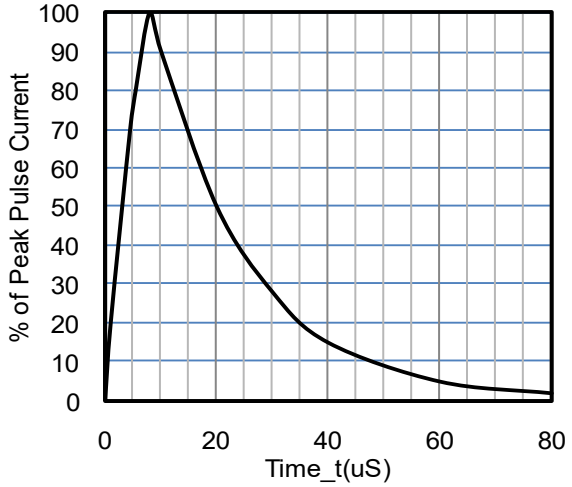
Peak Pulse Power vs. Pulse Time



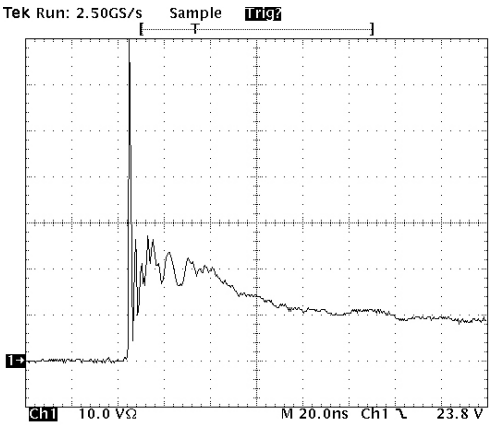
Clamping Voltage vs. Peak Pulse Current



Power Derating Curve



8 X 20μs Pulse Waveform



ESD Clamping Voltage

8 kV Contact per IEC61000−4−2

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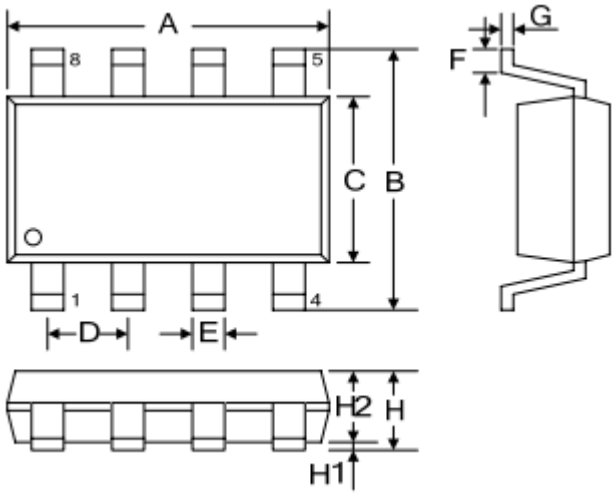
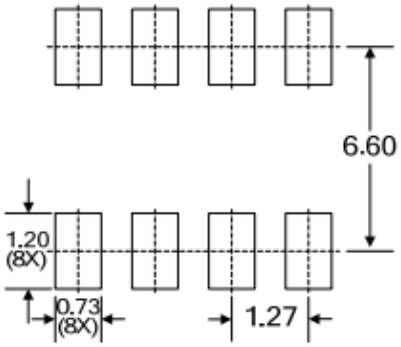
SO-8 Package Outline Drawing



Symbol	Dimension			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.80	5.00	0.189	0.197
B	5.80	6.20	0.228	0.244
C	3.80	4.00	0.150	0.157
D	1.27		0.050	
E	0.33	0.51	0.013	0.020
F	0.40	1.27	0.016	0.050
G	0.19	0.25	0.007	0.010
H	1.35	1.75	0.053	0.069
H1	0.10	0.25	0.004	0.010
H2	1.45		0.057	

Suggested Land Pattern



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